

L Number	Hits	Search Text	DB	Time stamp
15	2477	("silicon carbide" or SiC) and ("silicon dioxide" or oxide or "SiO.sub.2")	EPO; JPO	2002/09/16 14:49
16	380	((("silicon carbide" or SiC) and ("silicon dioxide" or oxide or "SiO.sub.2"))) and (oxidize or oxidation or oxidizing or oxidized)	EPO; JPO	2002/09/16 14:49
17	19	((("silicon carbide" or SiC) and ("silicon dioxide" or oxide or "SiO.sub.2"))) and (oxidize or oxidation or oxidizing or oxidized)) and (nitrogen or "NH.sub.3" or ammonia or nitric or nitrous or "N.sub.2 O")	EPO; JPO	2002/09/16 14:50
-	14598	("silicon carbide" or SiC) WITH ("silicon dioxide" or oxide or "SiO.sub.2")	USPAT; US-PGPUB	2002/09/16 14:48
-	10237	((("silicon carbide" or SiC) WITH ("silicon dioxide" or oxide or "SiO.sub.2"))) and (nitrogen or N or nitric or nitrous)	USPAT; US-PGPUB	2002/09/10 14:07
-	706	((("silicon carbide" or SiC) WITH ("silicon dioxide" or oxide or "SiO.sub.2"))) and (nitrogen or N or nitric or nitrous)) and (semiconductor or "integrated circuit")) and (anneal or annealing)	USPAT; US-PGPUB	2002/09/10 18:27
-	635	(((((("silicon carbide" or SiC) WITH ("silicon dioxide" or oxide or "SiO.sub.2"))) and (nitrogen or N or nitric or nitrous)) and (semiconductor or "integrated circuit")) and (anneal or annealing)) and (thermal or oxidiz\$ or oxidation)	USPAT; US-PGPUB	2002/09/10 14:09
-	192	(((((("silicon carbide" or SiC) WITH ("silicon dioxide" or oxide or "SiO.sub.2"))) and (nitrogen or N or nitric or nitrous)) and (semiconductor or "integrated circuit")) and (anneal or annealing)) and (thermal or oxidiz\$ or oxidation)) and ammonia	USPAT; US-PGPUB	2002/09/10 14:14
-	11167	("silicon carbide" or SiC) and (("silicon dioxide" or oxide or "SiO.sub.2") SAME ((thermal or oxidiz\$ or oxidation) or (anneal or annealing or annealed) WITH (nitrogen or N or nitric or nitrous or ammonia))))	USPAT; US-PGPUB	2002/09/10 14:30
-	17064	(thermal or oxidiz\$ or oxidation or anneal or annealing or annealed) WITH (nitrogen or N or nitric or nitrous or ammonia) WITH (dioxide or oxide or "SiO.subs.2" or SiO)	USPAT; US-PGPUB	2002/09/10 14:33
-	129	((thermal or oxidiz\$ or oxidation or anneal or annealing or annealed) WITH (nitrogen or N or nitric or nitrous or ammonia) WITH (dioxide or oxide or "SiO.subs.2" or SiO)) same ("silicon carbide" or SiC)	USPAT; US-PGPUB	2002/09/10 15:39
-	55110	(anneal or annealing or heat or heating or temp or temperature) WITH (nitric or "N.sub.2 O" or "N.sub.20" or ammonia or ammonium)	USPAT; US-PGPUB	2002/09/10 19:04
-	430	((anneal or annealing or heat or heating or temp or temperature) WITH (nitric or "N.sub.2 O" or "N.sub.20" or ammonia or ammonium)) and (("silicon dioxide" or "silicon oxide" or "SiO.sub.2" or SiO) WITH ((thermal or thermally) ADJ2 (oxidation or oxidiz\$)))	USPAT; US-PGPUB	2002/09/10 18:48

-	27	((anneal or annealing or heat or heating or temp or temperature) WITH (nitric or "N.sub.2 O" or "N.sub.20" or ammonia or ammonium)) and ("silicon dioxide" or "silicon oxide" or "SiO.sub.2" or SiO) WITH ((thermal or thermally) ADJ2 (oxidation or oxidiz\$)))) and ("silicon carbide" or SiC)	USPAT; US-PGPUB	2002/09/10 18:48
-	68	((anneal or annealing or heat or heating or temp or temperature) WITH (nitric or "N.sub.2 O" or "N.sub.20" or ammonia or ammonium) WITH (oxide)) SAME (SiC or carbide)	USPAT; US-PGPUB	2002/09/10 19:05